

AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

Claims 1-18 (Canceled)

19. **(Currently Amended)** A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component silane and a second chemical component arsine, the method comprising the steps of:
- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis;
 - b. baffling, by said plurality of substrates, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; and
 - c. causing substantially only the first chemical components of the silane to be thermal chemical vapor deposited onto ones of said plurality of substrates; and.
 - d. subsequent to step c, removing, in a chamber separate from said enclosure, the second chemical component arsine from the exhaust gas.
20. **(Currently Amended)** A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step c) wherein the step of removing the arsine includes adsorbing the arsine in an adsorber.
21. **(Previously Presented)** A method according to claim 19, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 800°C.

22. **(Previously Presented)** A method according to claim 21, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 1100°C.

23. **(Currently Amended)** A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is toxic, the step of baffling is performed by forcing the exhaust gas to flow through a plurality of apertures formed in said plurality of substrates.

24. **(Canceled)**

25. **(Currently Amended)** A method according to claim 19, further comprising after step c) the steps of:

- a. removing said at least one of said plurality of substrates from said enclosure;
- b. cleaning said at least one of said plurality of substrates of any film deposited thereon;
- c. installing said at least one of said plurality of substrates in said enclosure; and
- d. again causing only the first chemical components of the silane to be chemical vapor deposited onto said at least one plurality of substrates.

26. **(Currently Amended)** A method of scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a carrier gassilane and a dopant gasarsine, the carrier gassilane comprising a component depositable by thermal chemical vapor deposition, the method comprising the steps of:

- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis, said plurality of substrates including a plurality of apertures formed therein;

- b. baffling, by said plurality of substrates, the exhaust gas within said chamber by forcing the exhaust gas to flow substantially only through said plurality of apertures so as to increase the residence time of the exhaust gas within said chamber; and
 - c. causing a layer of the component of the carrier gassilane to be thermal chemical vapor deposited onto ones of said plurality of substrates; and
 - d. removing, in a chamber separate from said enclosure, the dopant gasarsine from the exhaust gas after performing step c).
27. **(Currently Amended)** A method according to claim 26, further comprising the step of removing the dopant gas from the exhaust gas after performing step c) wherein the step of removing the arsine includes adsorbing the arsine in an adsorber.
28. **(Previously Presented)** A method according to claim 26, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 800°C.
29. **(Previously Presented)** A method according to claim 28, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 1100°C.
30. **(Canceled)**
31. **(Canceled)**
32. **(Previously Presented)** A method according to claim 26, wherein said enclosure contains a plurality of substrates arranged in series with one another along said chamber so as to baffle flow of the exhaust gas.

33. (Canceled)

34. (Canceled)

35. (Canceled).

36. (Canceled)

37. (Previously Presented) A method according to claim 19, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.

38. (Canceled)